

Abstract of the Disclosure

A method for fabricating a conducting layer pattern using a hard mask of which an upper surface is flattened by the use of ArF exposure light source. The method includes the steps of: forming a conducting layer on a semiconductor substrate; forming a first hard mask layer, a second hard mask layer and a third hard mask layer on the conducting layer in order; forming a photoresist pattern on the third hard mask layer using an ArF exposure light source in order to form a predetermined pattern; forming a first hard mask pattern by etching the third hard mask layer using the photoresist pattern as an etching mask; forming a second hard mask pattern by etching the second hard mask layer using the first hard mask pattern as an etching mask; removing the first hard mask pattern; and etching the first hard mask layer and the conducting layer using the second hard mask pattern as an etching mask and forming a stacked hard mask pattern having the conducting layer and the second and first hard mask patterns, whereby a spire-shaped pattern is removed from the stacked hard mask pattern.